

AMENDMENTS TO THE CLAIMS

Claims 1-18 (Canceled)

Claim 19 (New) A method of growing a single crystal comprising:
bringing a seed crystal into contact with a raw material melt which is heated and melted within
a crucible and growing a single crystal; and

rotating the crucible without rotating a stirring member in the crucible in the raw material melt
during said growing, the stirring member being selected from one of a blade member having a screw
form and a baffle member comprising a plurality of baffle plate fragments, so as to stir the raw
material melt in the crucible;

wherein said growing a single crystal includes slowly cooling the raw material melt with which
the seed crystal makes contact below a liquid level of the raw material melt to precipitate the single
crystal on the surface of the seed crystal.

Claim 20 (New) The method of claim 19, wherein the seed crystal is rotated during said rotating
the crucible.

Claim 21 (New) The method of claim 20, wherein said growing comprises growing a single
crystal of an oxide.

Claim 22 (New) The method of claim 21, said growing a single crystal of an oxide comprises
growing a single crystal of a borate type oxide.

Claim 23 (New) The method of claim 22, wherein the borate type oxide is $CsLiB_5O_{10}$ or an
oxide obtained by partially substituting at least one of Cs and Li of $CsLiB_5O_{10}$ with at least one type
oxide among other alkali metal elements and alkali earth metal elements.

Claim 24 (New) The method of claim 23, wherein the oxide is doped with at least one of Al and Ga elements.

Claim 25 (New) The method of claim 22, wherein the borate type oxide is represented by $Gd_xY_{1-x}Ca_4O(BO_3)_3$ ($0 < x < 1$) and said growing comprises a pulling method.

Claim 26 (New) The method of claim 21, wherein the single crystal of an oxide is $LiNbO_3$, $LiTaO_3$, a high-temperature superconductive oxide material or a heat-electricity-conversion oxide material.

Claim 27 (New) The method of claim 19, wherein said growing comprises growing a single crystal of an oxide.

Claim 28 (New) The method of claim 27, said growing a single crystal of an oxide comprises growing a single crystal of a borate type oxide.

Claim 29 (New) The method of claim 28, wherein the borate type oxide is $CsLiB_5O_{10}$ or an oxide obtained by partially substituting at least one of Cs and Li of $CsLiB_5O_{10}$ with at least one type among other alkali metal elements and alkali earth metal elements.

Claim 30 (New) The method of claim 29, wherein the oxide is doped with at least one of Al and Ga elements.

Claim 31 (New) The method of claim 28, wherein the borate type oxide is represented by $Gd_xY_{1-x}Ca_4O(BO_3)_3$ ($0 < x < 1$) and said growing comprises a pulling method.

Claim 32 (New) The method of claim 27, wherein the single crystal of an oxide is LiNbO₃, LiTaO₃, a high-temperature superconductive oxide material or a heat-electricity-conversion oxide material.

Claim 33 (New) A growing apparatus for growing a single crystal by bringing a seed crystal into contact with a heated and melted raw material melt, comprising:

 a crucible for holding the raw material melt therein;
 a stirring member in the crucible for stirring the raw material melt in the crucible during growing of the single crystal, the stirring member being selected from one of a blade member having a screw form and a baffle member comprising a plurality of baffle plate fragments;
 a rotating device for rotating the crucible; and
 a cooling mechanism for slowly cooling the raw material melt, with which the seed crystal makes contact, below a liquid level of the raw material melt.

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Claim 34 (New) The growing apparatus of claim 33, and further comprising a mechanism for rotating the seed crystal.

Claim 35 (New) The growing apparatus of claim 33, wherein said rotating device and said stirring member are arranged such that said rotating device can rotate said crucible without rotating said stirring member.

Claim 36 (New) A growing apparatus for growing a single crystal by bringing a seed crystal into contact with a heated and melted raw material melt, comprising:

 a crucible for holding the raw material melt therein;
 a stirring member in the crucible for stirring the raw material melt in the crucible during growing of the single crystal, the stirring member being selected from one of a blade member having a screw form and a baffle member comprising a plurality of baffle plate fragments;

a rotating device for rotating the crucible, wherein said rotating device and said stirring member are arranged such that said rotating device can rotate said crucible without rotating said stirring member.

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